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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	15
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 6x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	24-WFQFN Exposed Pad
Supplier Device Package	24-HWQFN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f1017cana-u0

O ROM, RAM capacities

Flash ROM	Data flash	RAM	RL78/G13					
			20 pins	24 pins	25 pins	30 pins	32 pins	36 pins
128 KB	8 KB	12 KB	—	—	—	R5F100AG	R5F100BG	R5F100CG
	—		—	—	—	R5F101AG	R5F101BG	R5F101CG
96 KB	8 KB	8 KB	—	—	—	R5F100AF	R5F100BF	R5F100CF
	—		—	—	—	R5F101AF	R5F101BF	R5F101CF
64 KB	4 KB	4 KB Note	R5F1006E	R5F1007E	R5F1008E	R5F100AE	R5F100BE	R5F100CE
	—		R5F1016E	R5F1017E	R5F1018E	R5F101AE	R5F101BE	R5F101CE
48 KB	4 KB	3 KB Note	R5F1006D	R5F1007D	R5F1008D	R5F100AD	R5F100BD	R5F100CD
	—		R5F1016D	R5F1017D	R5F1018D	R5F101AD	R5F101BD	R5F101CD
32 KB	4 KB	2 KB	R5F1006C	R5F1007C	R5F1008C	R5F100AC	R5F100BC	R5F100CC
	—		R5F1016C	R5F1017C	R5F1018C	R5F101AC	R5F101BC	R5F101CC
16 KB	4 KB	2 KB	R5F1006A	R5F1007A	R5F1008A	R5F100AA	R5F100BA	R5F100CA
	—		R5F1016A	R5F1017A	R5F1018A	R5F101AA	R5F101BA	R5F101CA

Flash ROM	Data flash	RAM	RL78/G13							
			40 pins	44 pins	48 pins	52 pins	64 pins	80 pins	100 pins	128 pins
512 KB	8 KB	32 KB Note	—	R5F100FL	R5F100GL	R5F100JL	R5F100LL	R5F100ML	R5F100PL	R5F100SL
	—		—	R5F101FL	R5F101GL	R5F101JL	R5F101LL	R5F101ML	R5F101PL	R5F101SL
384 KB	8 KB	24 KB	—	R5F100FK	R5F100GK	R5F100JK	R5F100LK	R5F100MK	R5F100PK	R5F100SK
	—		—	R5F101FK	R5F101GK	R5F101JK	R5F101LK	R5F101MK	R5F101PK	R5F101SK
256 KB	8 KB	20 KB Note	—	R5F100FJ	R5F100GJ	R5F100JJ	R5F100LJ	R5F100MJ	R5F100PJ	R5F100SJ
	—		—	R5F101FJ	R5F101GJ	R5F101JJ	R5F101LJ	R5F101MJ	R5F101PJ	R5F101SJ
192 KB	8 KB	16 KB	R5F100EH	R5F100FH	R5F100GH	R5F100JH	R5F100LH	R5F100MH	R5F100PH	R5F100SH
	—		R5F101EH	R5F101FH	R5F101GH	R5F101JH	R5F101LH	R5F101MH	R5F101PH	R5F101SH
128 KB	8 KB	12 KB	R5F100EG	R5F100FG	R5F100GG	R5F100JG	R5F100LG	R5F100MG	R5F100PG	—
	—		R5F101EG	R5F101FG	R5F101GG	R5F101JG	R5F101LG	R5F101MG	R5F101PG	—
96 KB	8 KB	8 KB	R5F100EF	R5F100FF	R5F100GF	R5F100JF	R5F100LF	R5F100MF	R5F100PF	—
	—		R5F101EF	R5F101FF	R5F101GF	R5F101JF	R5F101LF	R5F101MF	R5F101PF	—
64 KB	4 KB	4 KB Note	R5F100EE	R5F100FE	R5F100GE	R5F100JE	R5F100LE	—	—	—
	—		R5F101EE	R5F101FE	R5F101GE	R5F101JE	R5F101LE	—	—	—
48 KB	4 KB	3 KB Note	R5F100ED	R5F100FD	R5F100GD	R5F100JD	R5F100LD	—	—	—
	—		R5F101ED	R5F101FD	R5F101GD	R5F101JD	R5F101LD	—	—	—
32 KB	4 KB	2 KB	R5F100EC	R5F100FC	R5F100GC	R5F100JC	R5F100LC	—	—	—
	—		R5F101EC	R5F101FC	R5F101GC	R5F101JC	R5F101LC	—	—	—
16 KB	4 KB	2 KB	R5F100EA	R5F100FA	R5F100GA	—	—	—	—	—
	—		R5F101EA	R5F101FA	R5F101GA	—	—	—	—	—

Note The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = 6 to 8, A to C, E to G, J, L): Start address FF300H

R5F100xE, R5F101xE (x = 6 to 8, A to C, E to G, J, L): Start address FEF00H

R5F100xJ, R5F101xJ (x = F, G, J, L, M, P): Start address FAF00H

R5F100xL, R5F101xL (x = F, G, J, L, M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

Table 1-1. List of Ordering Part Numbers

(8/12)

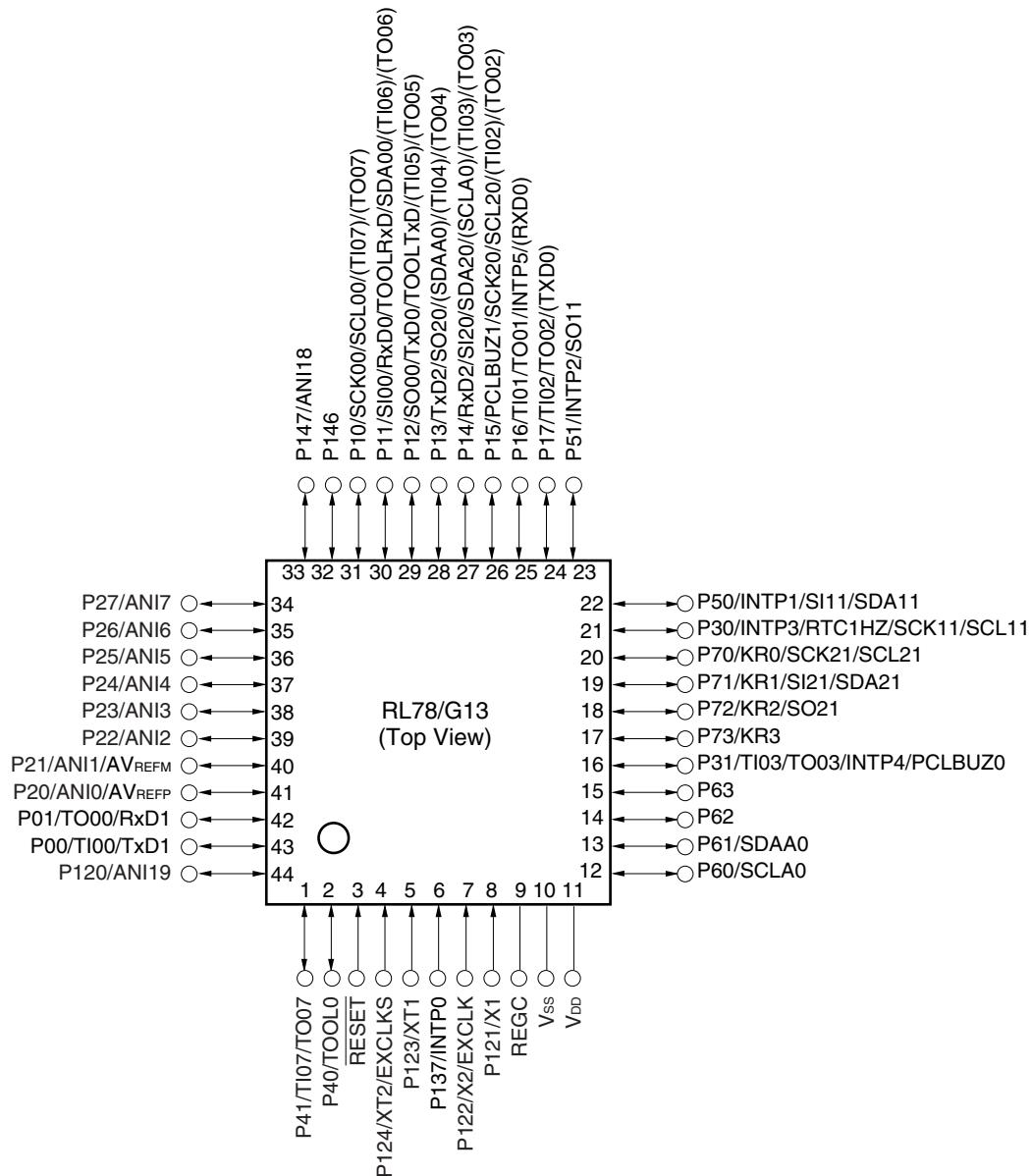
Pin count	Package	Data flash	Fields of Application ^{Note}	Ordering Part Number
64 pins	64-pin plastic LQFP (12 × 12 mm, 0.65 mm pitch)	Mounted	A D G	R5F100LCAFA#V0, R5F100LDAFA#V0, R5F100LEAFA#V0, R5F100LFAFA#V0, R5F100LGAFA#V0, R5F100LHAFA#V0, R5F100LJAFA#V0, R5F100LKAFA#V0, R5F100LLAFA#V0 R5F100LCAFA#X0, R5F100LDAFA#X0, R5F100LEAFA#X0, R5F100LFAFA#X0, R5F100LGAFA#X0, R5F100LHAFA#X0, R5F100LJAFA#X0, R5F100LKAFA#X0, R5F100LLAFA#X0 R5F100LCDFA#V0, R5F100LDDFA#V0, R5F100LEDFA#V0, R5F100LF DFA#V0, R5F100LGDFA#V0, R5F100LHDFA#V0, R5F100LJDFA#V0, R5F100LK DFA#V0, R5F100LLDFA#V0 R5F100LCDFA#X0, R5F100LDDFA#X0, R5F100LEDFA#X0, R5F100LF DFA#X0, R5F100LGDFA#X0, R5F100LHDFA#X0, R5F100LJDFA#X0, R5F100LK DFA#X0, R5F100LLDFA#X0 R5F100LCGFA#V0, R5F100LDGFA#V0, R5F100LEGFA#V0, R5F100LFGFA#V0 R5F100LCGFA#X0, R5F100LDGFA#X0, R5F100LEGFA#X0, R5F100LFGFA#X0 R5F100LGGFA#V0, R5F100LHGFA#V0, R5F100LJGFA#V0 R5F100LGGFA#X0, R5F100LHGFA#X0, R5F100LJGFA#X0
		Not mounted	A D	R5F101LCAFA#V0, R5F101LDAFA#V0, R5F101LEAFA#V0, R5F101LFAFA#V0, R5F101LGAFA#V0, R5F101LHAFA#V0, R5F101LJAFA#V0, R5F101LKAFA#V0, R5F101LLAFA#V0 R5F101LCAFA#X0, R5F101LDAFA#X0, R5F101LEAFA#X0, R5F101LFAFA#X0, R5F101LGAFA#X0, R5F101LHAFA#X0, R5F101LJAFA#X0, R5F101LKAFA#X0, R5F101LLAFA#X0 R5F101LCDFA#V0, R5F101LDDFA#V0, R5F101LEDFA#V0, R5F101LF DFA#V0, R5F101LGDFA#V0, R5F101LHDFA#V0, R5F101LJDFA#V0, R5F101LK DFA#V0, R5F101LLDFA#V0 R5F101LCDFA#X0, R5F101LDDFA#X0, R5F101LEDFA#X0, R5F101LF DFA#X0, R5F101LGDFA#X0, R5F101LHDFA#X0, R5F101LJDFA#X0, R5F101LK DFA#X0, R5F101LLDFA#X0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.8 44-pin products

- 44-pin plastic LQFP (10 × 10 mm, 0.8 mm pitch)



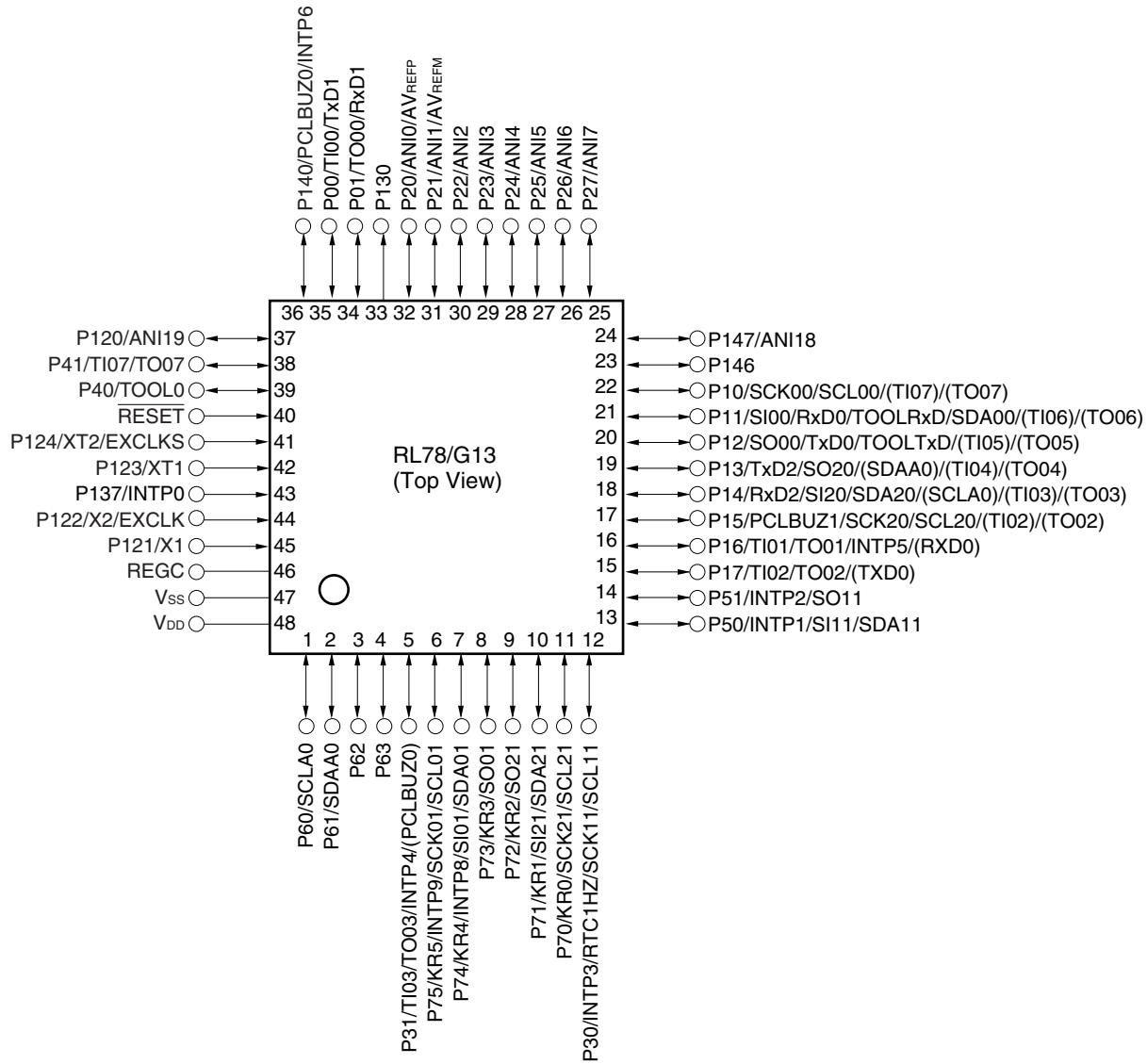
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.3.9 48-pin products

- 48-pin plastic LFQFP (7 × 7 mm, 0.5 mm pitch)

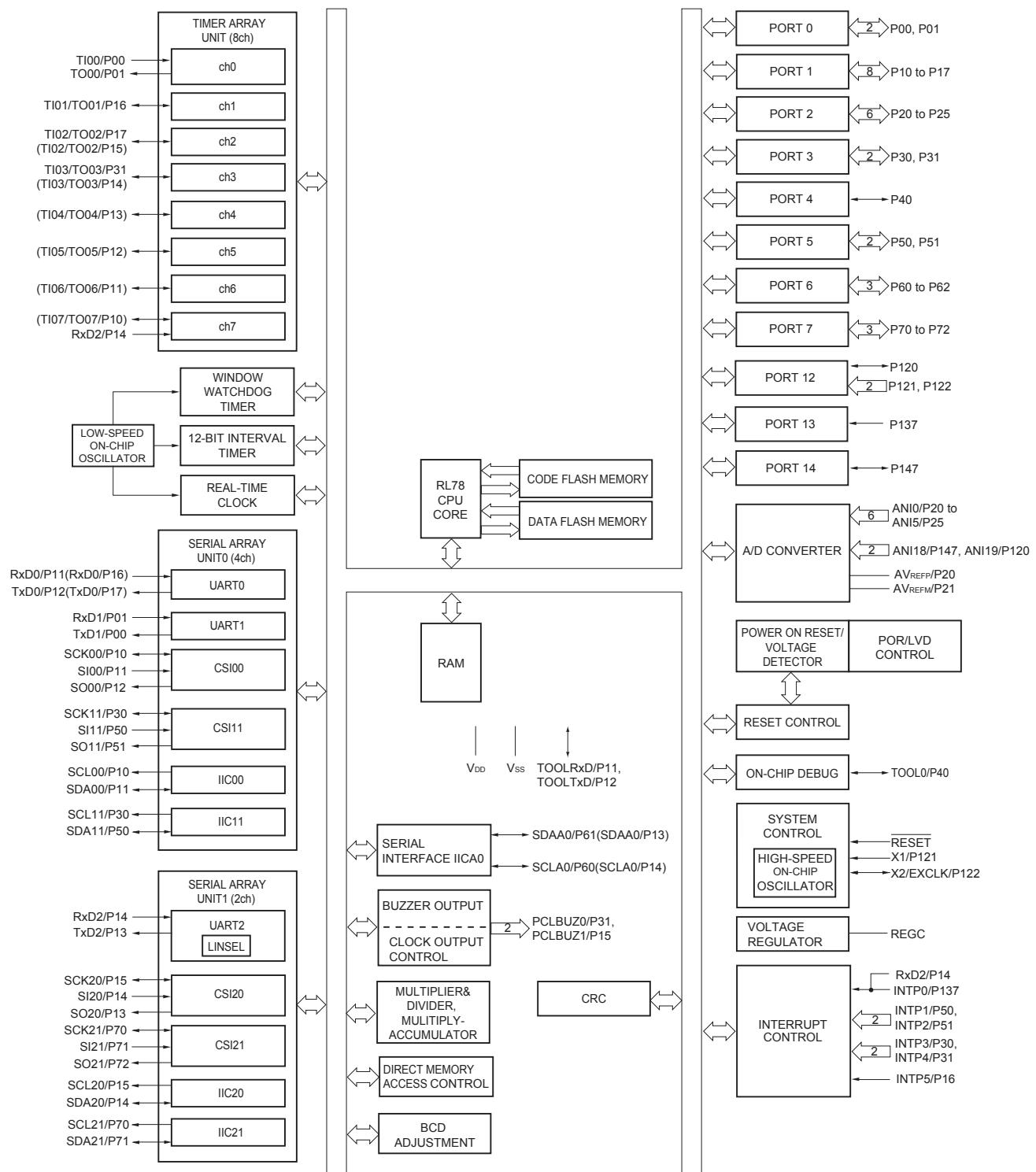


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.6 36-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

- Notes**
1. Total current flowing into V_{DD} , EV_{DD0} , and EV_{DD1} , including the input leakage current flowing when the level of the input pin is fixed to V_{DD} , EV_{DD0} , and EV_{DD1} , or V_{SS} , EV_{SS0} , and EV_{SS1} . The values below the MAX. column include the peripheral operation current . However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 2. During HALT instruction execution by flash memory.
 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 4. When high-speed system clock and subsystem clock are stopped.
 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When $RTCLPC = 1$ and setting ultra-low current consumption ($AMPHS1 = 1$). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:	$2.7 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 32 MHz
	$2.4 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 16 MHz
LS (low-speed main) mode:	$1.8 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 8 MHz
	LV (low-voltage main) mode: $1.6 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 4 MHz
 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.

- Remarks**
1. f_{MX} : High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 2. f_{IH} : High-speed on-chip oscillator clock frequency
 3. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)
 4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^\circ\text{C}$

6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter operates in an operation mode or the HALT mode.
7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of I_{DD1} , I_{DD2} or I_{DD3} and I_{LVD} when the LVD circuit is in operation.
8. Current flowing only during data flash rewrite.
9. Current flowing only during self programming.
10. For shift time to the SNOOZE mode, see **18.3.3 SNOOZE mode**.

Remarks

- 1. f_{IL} : Low-speed on-chip oscillator clock frequency
- 2. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)
- 3. f_{CLK} : CPU/peripheral hardware clock frequency
- 4. Temperature condition of the TYP. value is $T_A = 25^\circ\text{C}$

3. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V ≤ EV_{DD0} < 4.0 V and 2.3 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{\left(\frac{1}{\text{Transfer rate}}\right) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

4. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.
5. Use it with EV_{DD0} ≥ V_b.
6. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 1.8 V ≤ EV_{DD0} < 3.3 V and 1.6 V ≤ V_b ≤ 2.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \text{ [bps]}$$

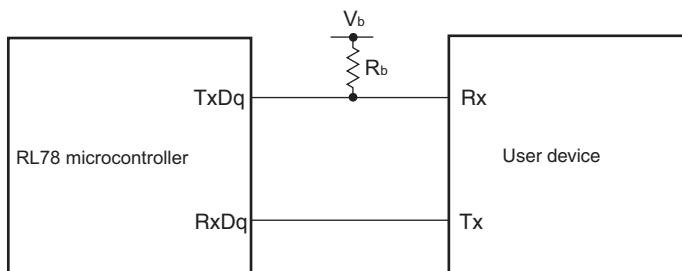
$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{\left(\frac{1}{\text{Transfer rate}}\right) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

7. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 6 above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)



**(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)
(2/3)**

($T_A = -40$ to $+85^\circ\text{C}$, $1.8 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Slp setup time (to SCKp \uparrow) ^{Note 1}	tsIK1	4.0 V \leq EV _{DD0} \leq 5.5 V, 2.7 V \leq V _b \leq 4.0 V, C _b = 30 pF, R _b = 1.4 k Ω	81		479		479		ns
		2.7 V \leq EV _{DD0} < 4.0 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 30 pF, R _b = 2.7 k Ω	177		479		479		ns
		1.8 V \leq EV _{DD0} < 3.3 V, 1.6 V \leq V _b \leq 2.0 V ^{Note 2} , C _b = 30 pF, R _b = 5.5 k Ω	479		479		479		ns
Slp hold time (from SCKp \uparrow) ^{Note 1}	tKS11	4.0 V \leq EV _{DD0} \leq 5.5 V, 2.7 V \leq V _b \leq 4.0 V, C _b = 30 pF, R _b = 1.4 k Ω	19		19		19		ns
		2.7 V \leq EV _{DD0} < 4.0 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 30 pF, R _b = 2.7 k Ω	19		19		19		ns
		1.8 V \leq EV _{DD0} < 3.3 V, 1.6 V \leq V _b \leq 2.0 V ^{Note 2} , C _b = 30 pF, R _b = 5.5 k Ω	19		19		19		ns
Delay time from SCKp \downarrow to SO _p output ^{Note 1}	tKS01	4.0 V \leq EV _{DD0} \leq 5.5 V, 2.7 V \leq V _b \leq 4.0 V, C _b = 30 pF, R _b = 1.4 k Ω		100		100		100	ns
		2.7 V \leq EV _{DD0} < 4.0 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 30 pF, R _b = 2.7 k Ω		195		195		195	ns
		1.8 V \leq EV _{DD0} < 3.3 V, 1.6 V \leq V _b \leq 2.0 V ^{Note 2} , C _b = 30 pF, R _b = 5.5 k Ω		483		483		483	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. Use it with EV_{DD0} \geq V_b.

Caution Select the TTL input buffer for the Slp pin and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the SO_p pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.

Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

4. Values when the conversion time is set to 57 μs (min.) and 95 μs (max.).

5. Refer to **2.6.2 Temperature sensor/internal reference voltage characteristics**.

2.8 Flash Memory Programming Characteristics

(TA = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	f _{CLK}	1.8 V ≤ V _{DD} ≤ 5.5 V	1		32	MHz
Number of code flash rewrites Notes 1, 2, 3	C _{erwr}	Retained for 20 years TA = 85°C	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 years TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C	100,000			
		Retained for 20 years TA = 85°C	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite.

The retaining years are until next rewrite after the rewrite.

2. When using flash memory programmer and Renesas Electronics self programming library
3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

(TA = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS $T_A = -40$ to $+105^\circ\text{C}$)

This chapter describes the following electrical specifications.

Target products G: Industrial applications $T_A = -40$ to $+105^\circ\text{C}$
R5F100xxGxx

- Cautions**
1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 2. With products not provided with an EV_{DD0}, EV_{DD1}, EV_{SS0}, or EV_{SS1} pin, replace EV_{DD0} and EV_{DD1} with V_{DD}, or replace EV_{SS0} and EV_{SS1} with V_{SS}.
 3. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 Functions for each product.
 4. Please contact Renesas Electronics sales office for derating of operation under $T_A = +85^\circ\text{C}$ to $+105^\circ\text{C}$. Derating is the systematic reduction of load for the sake of improved reliability.

Remark When RL78/G13 is used in the range of $T_A = -40$ to $+85^\circ\text{C}$, see **CHAPTER 2 ELECTRICAL SPECIFICATIONS ($T_A = -40$ to $+85^\circ\text{C}$)**.

There are following differences between the products "G: Industrial applications ($T_A = -40$ to $+105^\circ\text{C}$)" and the products "A: Consumer applications, and D: Industrial applications".

Parameter	Application	
	A: Consumer applications, D: Industrial applications	G: Industrial applications
Operating ambient temperature	$T_A = -40$ to $+85^\circ\text{C}$	$T_A = -40$ to $+105^\circ\text{C}$
Operating mode Operating voltage range	HS (high-speed main) mode: $2.7 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @1 MHz to 32 MHz $2.4 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @1 MHz to 16 MHz LS (low-speed main) mode: $1.8 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @1 MHz to 8 MHz LV (low-voltage main) mode: $1.6 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @1 MHz to 4 MHz	HS (high-speed main) mode only: $2.7 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @1 MHz to 32 MHz $2.4 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @1 MHz to 16 MHz
High-speed on-chip oscillator clock accuracy	$1.8 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ $\pm 1.0\% @ T_A = -20$ to $+85^\circ\text{C}$ $\pm 1.5\% @ T_A = -40$ to -20°C $1.6 \text{ V} \leq V_{DD} < 1.8 \text{ V}$ $\pm 5.0\% @ T_A = -20$ to $+85^\circ\text{C}$ $\pm 5.5\% @ T_A = -40$ to -20°C	$2.4 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ $\pm 2.0\% @ T_A = +85$ to $+105^\circ\text{C}$ $\pm 1.0\% @ T_A = -20$ to $+85^\circ\text{C}$ $\pm 1.5\% @ T_A = -40$ to -20°C
Serial array unit	UART CSI: $f_{CLK}/2$ (supporting 16 Mbps), $f_{CLK}/4$ Simplified I ² C communication	UART CSI: $f_{CLK}/4$ Simplified I ² C communication
I ² CA	Normal mode Fast mode Fast mode plus	Normal mode Fast mode
Voltage detector	Rise detection voltage: 1.67 V to 4.06 V (14 levels) Fall detection voltage: 1.63 V to 3.98 V (14 levels)	Rise detection voltage: 2.61 V to 4.06 V (8 levels) Fall detection voltage: 2.55 V to 3.98 V (8 levels)

(Remark is listed on the next page.)

3.3.2 Supply current characteristics

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products

($T_A = -40$ to $+105^\circ\text{C}$, $2.4 \text{ V} \leq EV_{DD0} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = 0 \text{ V}$) (1/2)

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit	
Supply current <small>Note 1</small>	I_{DD1}	Operating mode	HS (high-speed main) mode <small>Note 5</small>	$f_{IH} = 32 \text{ MHz}^{\text{Note 3}}$	Basic operation	$V_{DD} = 5.0 \text{ V}$		2.1		mA	
					Normal operation	$V_{DD} = 3.0 \text{ V}$		2.1		mA	
					$V_{DD} = 5.0 \text{ V}$		4.6	7.5		mA	
					$V_{DD} = 3.0 \text{ V}$		4.6	7.5		mA	
					$V_{DD} = 5.0 \text{ V}$		3.7	5.8		mA	
					$V_{DD} = 3.0 \text{ V}$		3.7	5.8		mA	
					$V_{DD} = 5.0 \text{ V}$		2.7	4.2		mA	
					$V_{DD} = 3.0 \text{ V}$		2.7	4.2		mA	
		HS (high-speed main) mode <small>Note 5</small>		$f_{MX} = 20 \text{ MHz}^{\text{Note 2}}$, $V_{DD} = 5.0 \text{ V}$	Normal operation	Square wave input		3.0	4.9	mA	
						Resonator connection		3.2	5.0	mA	
				$f_{MX} = 20 \text{ MHz}^{\text{Note 2}}$, $V_{DD} = 3.0 \text{ V}$	Normal operation	Square wave input		3.0	4.9	mA	
						Resonator connection		3.2	5.0	mA	
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}}$, $V_{DD} = 5.0 \text{ V}$	Normal operation	Square wave input		1.9	2.9	mA	
						Resonator connection		1.9	2.9	mA	
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}}$, $V_{DD} = 3.0 \text{ V}$	Normal operation	Square wave input		1.9	2.9	mA	
						Resonator connection		1.9	2.9	mA	
		Subsystem clock operation	$f_{SUB} = 32.768 \text{ kHz}$ <small>Note 4</small> $T_A = -40^\circ\text{C}$	Normal operation	Square wave input		4.1	4.9		μA	
						Resonator connection		4.2	5.0	μA	
						Square wave input		4.1	4.9	μA	
						Resonator connection		4.2	5.0	μA	
						Square wave input		4.2	5.5	μA	
			$f_{SUB} = 32.768 \text{ kHz}$ <small>Note 4</small> $T_A = +25^\circ\text{C}$	Normal operation		Resonator connection		4.3	5.6	μA	
						Square wave input		4.3	6.3	μA	
						Resonator connection		4.4	6.4	μA	
						Square wave input		4.6	7.7	μA	
						Resonator connection		4.7	7.8	μA	
			$f_{SUB} = 32.768 \text{ kHz}$ <small>Note 4</small> $T_A = +50^\circ\text{C}$	Normal operation	Square wave input		6.9	19.7		μA	
						Resonator connection		7.0	19.8	μA	

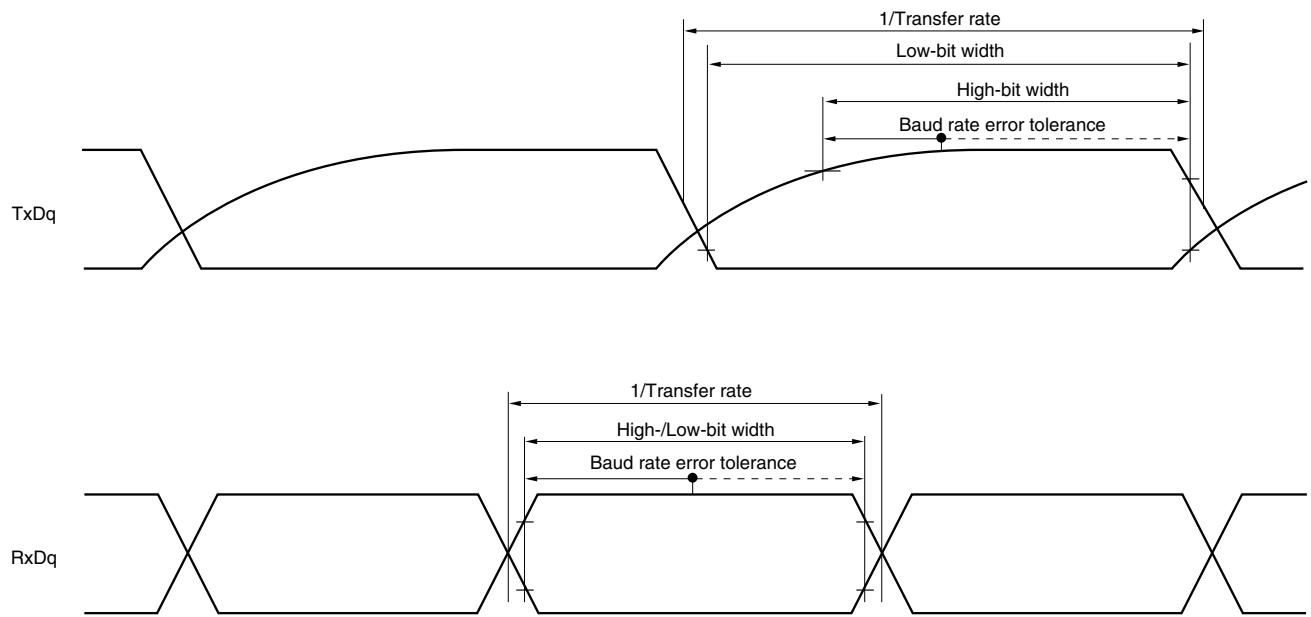
(Notes and Remarks are listed on the next page.)

(4) During communication at same potential (simplified I²C mode)(TA = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCL _r clock frequency	f _{SCL}	2.7 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ		400 ^{Note1}	kHz
		2.4 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ		100 ^{Note1}	kHz
Hold time when SCL _r = "L"	t _{LOW}	2.7 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ	1200		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	4600		ns
Hold time when SCL _r = "H"	t _{HIGH}	2.7 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ	1200		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	4600		ns
Data setup time (reception)	t _{SU:DAT}	2.7 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ	1/f _{MCK} + 220 ^{Note2}		ns
		2.4 V ≤ EV _{DD} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	1/f _{MCK} + 580 ^{Note2}		ns
Data hold time (transmission)	t _{HD:DAT}	2.7 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ	0	770	ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	0	1420	ns

Notes 1. The value must also be equal to or less than f_{MCK}/4.2. Set the f_{MCK} value to keep the hold time of SCL_r = "L" and SCL_r = "H".**Caution** Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCL_r pin by using port input mode register g (PIMg) and port output mode register h (POMh).

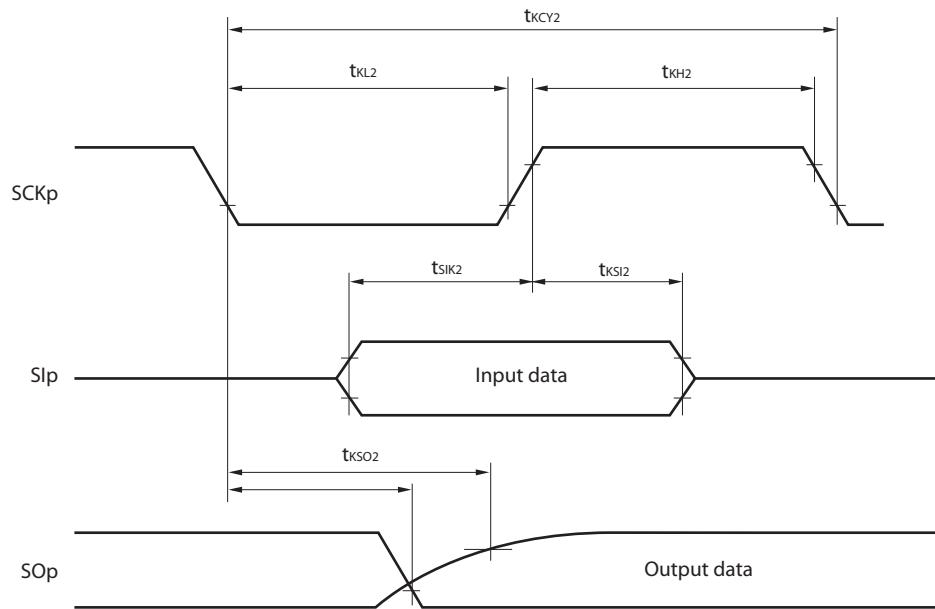
(Remarks are listed on the next page.)

UART mode bit width (during communication at different potential) (reference)

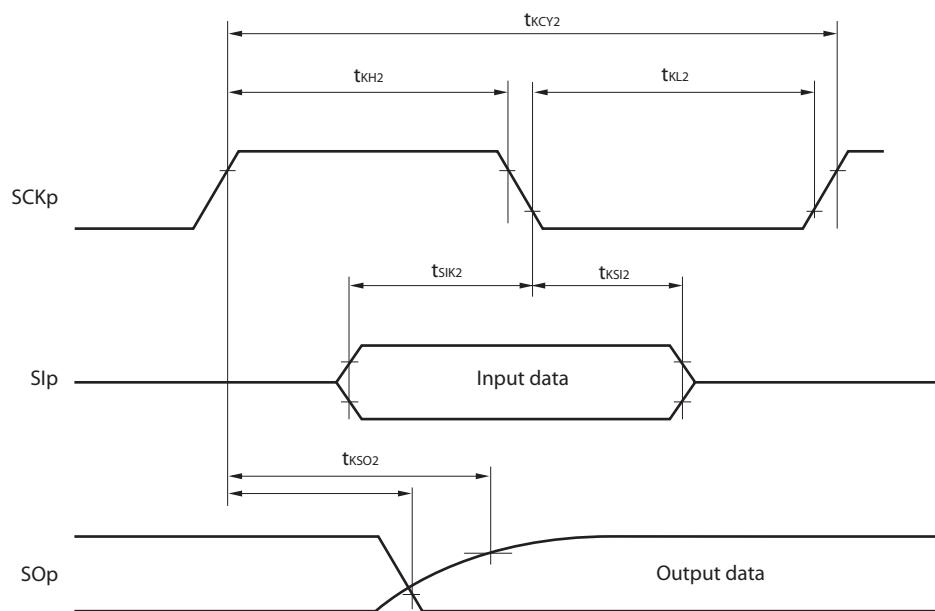
- Remarks**
1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance,
 $C_b[F]$: Communication line (TxDq) load capacitance, $V_b[V]$: Communication line voltage
 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 3. f_{MCK} : Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
 4. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

CSI mode serial transfer timing (slave mode) (during communication at different potential)

(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)

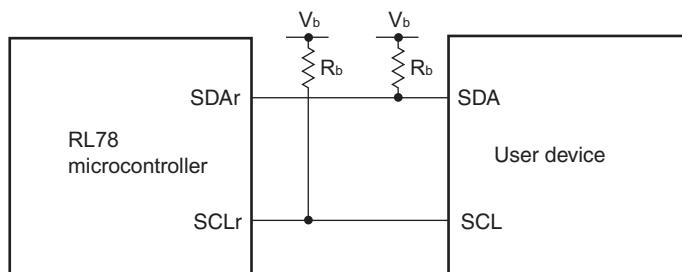
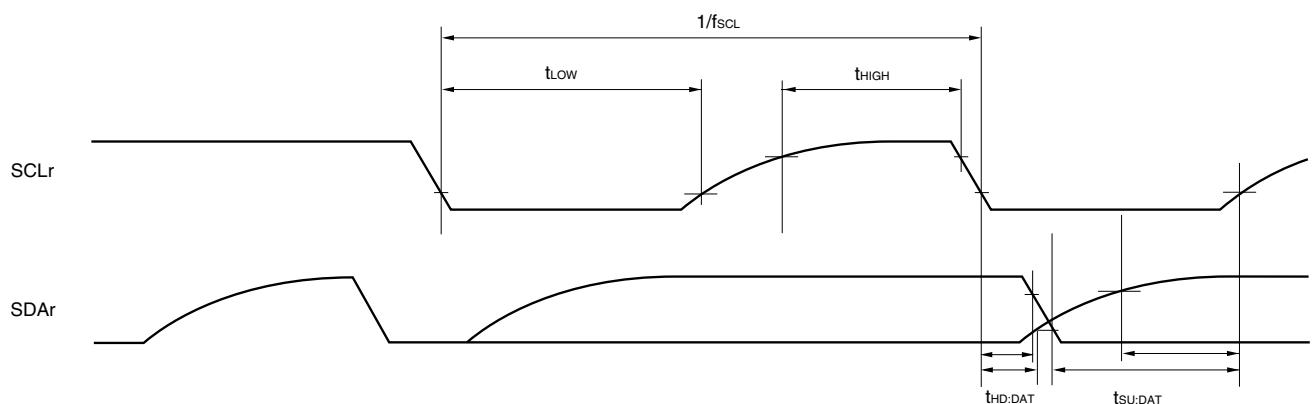
**CSI mode serial transfer timing (slave mode) (during communication at different potential)**

(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)

**Remarks** 1. p: CSI number ($p = 00, 01, 10, 20, 30, 31$), m: Unit number,n: Channel number ($mn = 00, 01, 02, 10, 12, 13$), g: PIM and POM number ($g = 0, 1, 4, 5, 8, 14$)

2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential.

Use other CSI for communication at different potential.

Simplified I²C mode connection diagram (during communication at different potential)**Simplified I²C mode serial transfer timing (during communication at different potential)**

Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

Remarks

1. $R_b[\Omega]$: Communication line (SDAr, SCLr) pull-up resistance, $C_b[F]$: Communication line (SDAr, SCLr) load capacitance, $V_b[V]$: Communication line voltage
2. r: IIC number (r = 00, 01, 10, 20, 30, 31), g: PIM, POM number (g = 0, 1, 4, 5, 8, 14)
3. f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))

- (2) When reference voltage (+) = $AV_{REFP}/ANI0$ (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = $AV_{REFM}/ANI1$ (ADREFM = 1), target pin : ANI16 to ANI26

(TA = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, 2.4 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{VSS0} = EV_{VSS1} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (-) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution EV _{DD0} ≤ AV _{REFP} = V _{DD} ^{Notes 3, 4}	2.4 V ≤ AV _{REFP} ≤ 5.5 V		1.2	±5.0	LSB
Conversion time	t _{CONV}	10-bit resolution Target pin : ANI16 to ANI26	3.6 V ≤ V _{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V _{DD} ≤ 5.5 V	3.1875		39	μs
			2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	10-bit resolution EV _{DD0} ≤ AV _{REFP} = V _{DD} ^{Notes 3, 4}	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±0.35	%FSR
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution EV _{DD0} ≤ AV _{REFP} = V _{DD} ^{Notes 3, 4}	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution EV _{DD0} ≤ AV _{REFP} = V _{DD} ^{Notes 3, 4}	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±3.5	LSB
Differential linearity error <small>Note 1</small>	DLE	10-bit resolution EV _{DD0} ≤ AV _{REFP} = V _{DD} ^{Notes 3, 4}	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±2.0	LSB
Analog input voltage	V _{AiN}	ANI16 to ANI26		0		AV _{REFP} and EV _{DD0}	V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When AV_{REFP} < V_{DD}, the MAX. values are as follows.

Overall error: Add ±1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add ±0.05%FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.

4. When AV_{REFP} < EV_{DD0} ≤ V_{DD}, the MAX. values are as follows.

Overall error: Add ±4.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

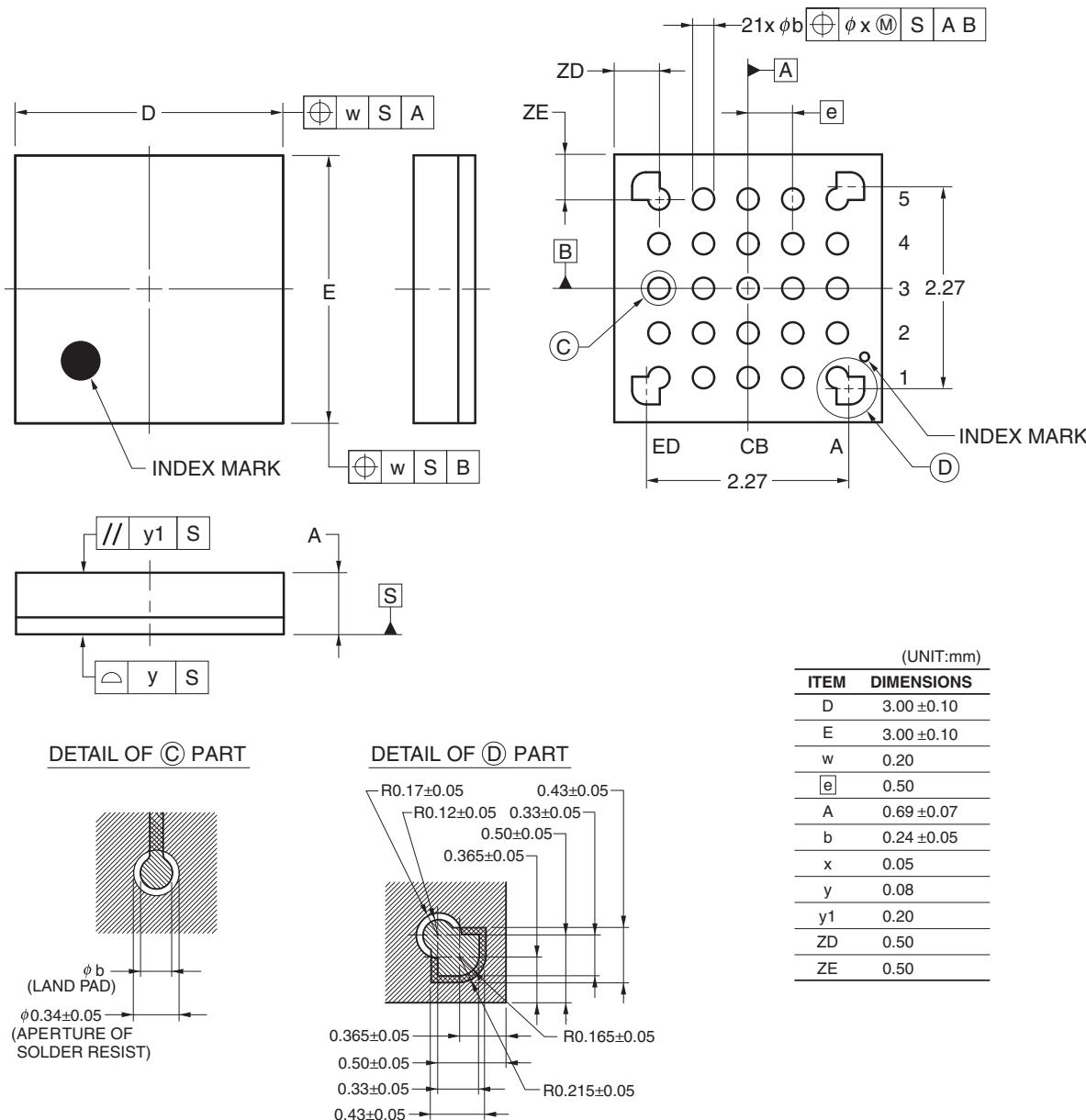
Zero-scale error/Full-scale error: Add ±0.20%FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

4.3 25-pin Products

R5F1008AALA, R5F1008CALA, R5F1008DALA, R5F1008EALA
 R5F1018AALA, R5F1018CALA, R5F1018DALA, R5F1018EALA
 R5F1008AGLA, R5F1008CGLA, R5F1008DGLA, R5F1008EGLA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA25-3x3-0.50	PWLG0025KA-A	P25FC-50-2N2-2	0.01

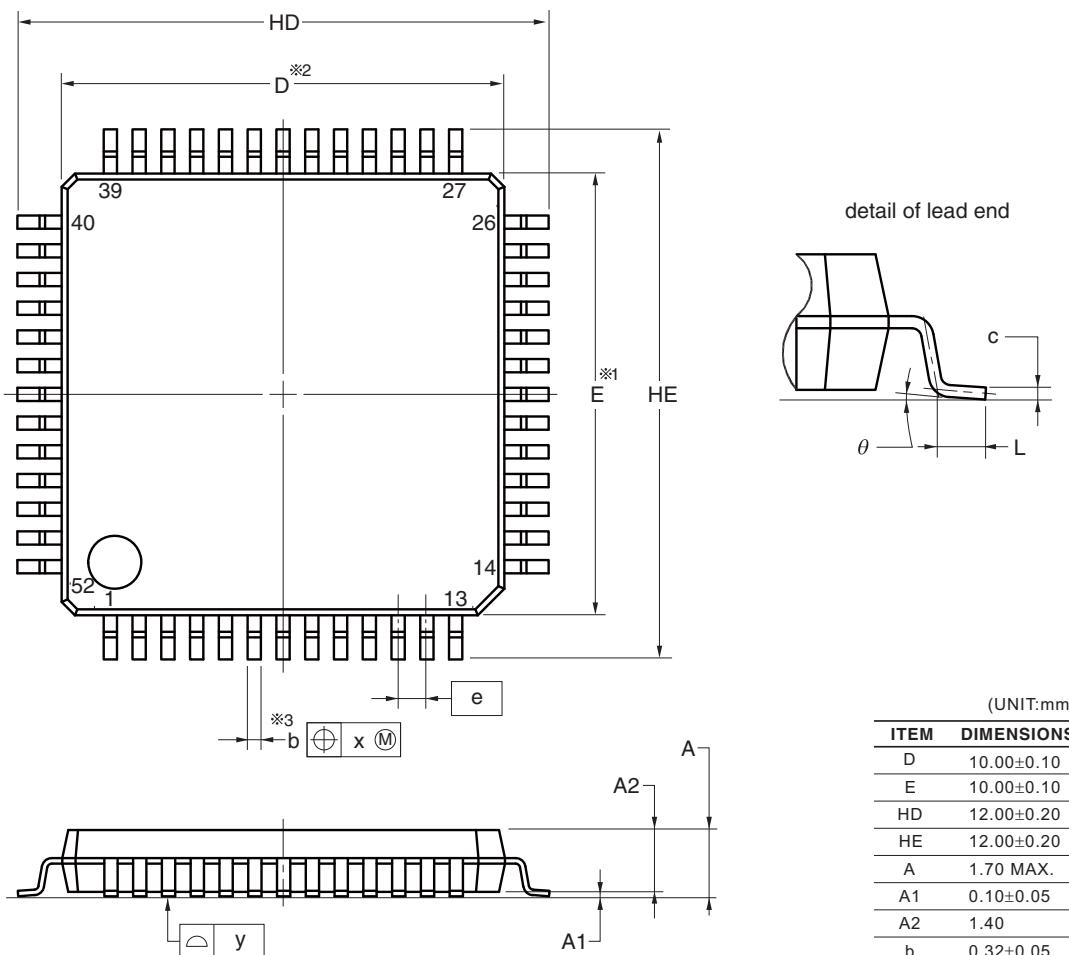


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4.10 52-pin Products

R5F100JCAFA, R5F100JDAFA, R5F100JEAF, R5F100JFAFA, R5F100JGAF, R5F100JHAF, R5F100JJAF,
 R5F100JKAF, R5F100JLAF
 R5F101JCAFA, R5F101JDAFA, R5F101JEAF, R5F101JFAFA, R5F101JGAF, R5F101JHAF, R5F101JJAF,
 R5F101JKAF, R5F101JLAF
 R5F100JCDFA, R5F100JDDFA, R5F100JEDFA, R5F100JFDFA, R5F100JGDFA, R5F100JHDFA, R5F100JJDF,
 R5F100JKDFA, R5F100JLDFA
 R5F101JCDFA, R5F101JDDFA, R5F101JEDFA, R5F101JFDFA, R5F101JGDFA, R5F101JHDFA, R5F101JJDF,
 R5F101JKDFA, R5F101JLDFA
 R5F100JCGFA, R5F100JDGFA, R5F100JEGFA, R5F100JFGFA, R5F100JGGFA, R5F100JHGFA, R5F100JJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP52-10x10-0.65	PLQP0052JA-A	P52GB-65-GBS-1	0.3



(UNIT:mm)	
ITEM	DIMENSIONS
D	10.00±0.10
E	10.00±0.10
HD	12.00±0.20
HE	12.00±0.20
A	1.70 MAX.
A1	0.10±0.05
A2	1.40
b	0.32±0.05
c	0.145±0.055
L	0.50±0.15
theta	0° to 8°
e	0.65
x	0.13
y	0.10

NOTE

1. Dimensions “*1” and “*2” do not include mold flash.
2. Dimension “*3” does not include trim offset.

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